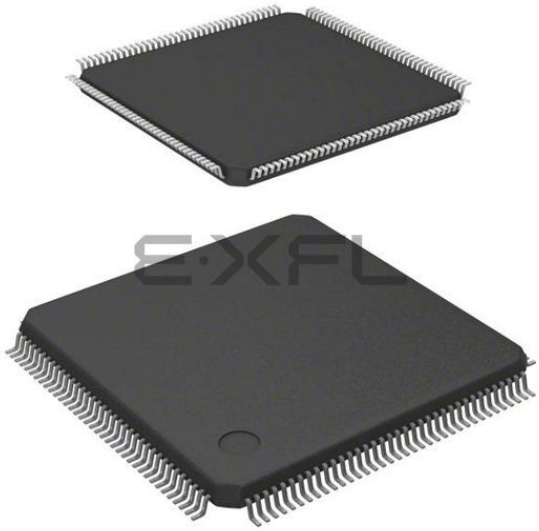

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Product Status	Active
Core Processor	e200z0h
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Peripherals	DMA, POR, PWM, WDT
Number of I/O	123
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 36x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560b40l5c6e0x

List of tables

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208[3]
PC[2]	PCR[34]	AF0 AF1 AF2 AF3 —	GPIO[34] SCK_1 CAN4TX[11] — EIRQ[5]	SIUL DSPI_1 FlexCAN_4 — SIUL	I/O I/O O — I	M	Tristate	50	78	117	A11
PC[3]	PCR[35]	AF0 AF1 AF2 AF3 — — —	GPIO[35] CS0_1 MA[0] — CAN1RX CAN4RX[11] EIRQ[6]	SIUL DSPI_1 ADC — FlexCAN_1 FlexCAN_4 SIUL	I/O I/O O — I I I	S	Tristate	49	77	116	B11
PC[4]	PCR[36]	AF0 AF1 AF2 AF3 — —	GPIO[36] — — — SIN_1 CAN3RX[11]	SIUL — — — DSPI_1 FlexCAN_3	I/O — — — I I	M	Tristate	62	92	131	B7
PC[5]	PCR[37]	AF0 AF1 AF2 AF3 —	GPIO[37] SOUT_1 CAN3TX[11] — EIRQ[7]	SIUL DSPI1 FlexCAN_3 — SIUL	I/O O O — I	M	Tristate	61	91	130	A7
PC[6]	PCR[38]	AF0 AF1 AF2 AF3	GPIO[38] LIN1TX — —	SIUL LINFlex_1 — —	I/O O — —	S	Tristate	16	25	36	R2
PC[7]	PCR[39]	AF0 AF1 AF2 AF3 — —	GPIO[39] — — — LIN1RX WKPU[12][4]	SIUL — — — LINFlex_1 WKPU	I/O — — — I I	S	Tristate	17	26	37	P3

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208[3]
PG[15]	PCR[111]	AF0 AF1 AF2 AF3	GPIO[111] E1UC[1] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	111	B13
PH[0]	PCR[112]	AF0 AF1 AF2 AF3 —	GPIO[112] E1UC[2] — — SIN1	SIUL eMIOS_1 — — DSPI_1	I/O I/O — — I	M	Tristate	—	—	93	F13
PH[1]	PCR[113]	AF0 AF1 AF2 AF3	GPIO[113] E1UC[3] SOUT1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O O —	M	Tristate	—	—	94	F14
PH[2]	PCR[114]	AF0 AF1 AF2 AF3	GPIO[114] E1UC[4] SCK_1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O I/O —	M	Tristate	—	—	95	F16
PH[3]	PCR[115]	AF0 AF1 AF2 AF3	GPIO[115] E1UC[5] CS0_1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O I/O —	M	Tristate	—	—	96	F15
PH[4]	PCR[116]	AF0 AF1 AF2 AF3	GPIO[116] E1UC[6] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	134	A6
PH[5]	PCR[117]	AF0 AF1 AF2 AF3	GPIO[117] E1UC[7] — —	SIUL eMIOS_1 — —	I/O I/O — —	S	Tristate	—	—	135	B6
PH[6]	PCR[118]	AF0 AF1 AF2 AF3	GPIO[118] E1UC[8] — MA[2]	SIUL eMIOS_1 — ADC	I/O I/O — O	M	Tristate	—	—	136	D5

11. Available only on SPC560Cx versions and SPC560B50B2 devices
12. Not available on SPC560B40L3 and SPC560B40L5 devices
13. Not available in 100 LQFP package
14. Available only on SPC560B50B2 devices
15. Not available on SPC560B44L3 devices

3.7 Nexus 2+ pins

In the LBGA208 package, eight additional debug pins are available (see *Table 7*).

Table 7. Nexus 2+ pin descriptions

Debug pin	Function	I/O direction	Pad type	Function after reset	Pin number		
					LQFP 100	LQFP 144	LBGA 208(1)
MCKO	Message clock out	O	F	—	—	—	T4
MDO0	Message data out 0	O	M	—	—	—	H15
MDO1	Message data out 1	O	M	—	—	—	H16
MDO2	Message data out 2	O	M	—	—	—	H14
MDO3	Message data out 3	O	M	—	—	—	H13
EVTI	Event in	I	M	Pull-up	—	—	K1
EVTO	Event out	O	M	—	—	—	L4
MSEO	Message start/end out	O	M	—	—	—	G16

1. LBGA208 available only as development package for Nexus2+.

3.8 Electrical characteristics

3.9 Introduction

This section contains electrical characteristics of the device as well as temperature and power considerations.

This product contains devices to protect the inputs against damage due to high static voltages. However, it is advisable to take precautions to avoid applying any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This could be done by the internal pull-up and pull-down, which is provided by the product for most general purpose pins.

The parameters listed in the following tables represent the characteristics of the device and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol “CC” for Controller Characteristics is included in the Symbol column.

3.11.2 NVUSRO[OSCILLATOR_MARGIN] field description

The fast external crystal oscillator consumption is dependent on the OSCILLATOR_MARGIN bit value. *Table 10* shows how NVUSRO[OSCILLATOR_MARGIN] controls the device configuration.

Table 10. OSCILLATOR_MARGIN field description

Value(1)	Description
0	Low consumption configuration (4 MHz/8 MHz)
1	High margin configuration (4 MHz/16 MHz)

1. Default manufacturing value is '1'. Value can be programmed by customer in Shadow Flash.

3.11.3 NVUSRO[WATCHDOG_EN] field description

The watchdog enable/disable configuration after reset is dependent on the WATCHDOG_EN bit value. *Table 11* shows how NVUSRO[WATCHDOG_EN] controls the device configuration.

Table 11. WATCHDOG_EN field description

Value(1)	Description
0	Disable after reset
1	Enable after reset

1. Default manufacturing value is '1'. Value can be programmed by customer in Shadow Flash.

3.12 Absolute maximum ratings

Table 12. Absolute maximum ratings

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS}	SR	Digital ground on VSS_HV pins	—	0	0	V
V_{DD}	SR	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	–0.3	6.0	V
V_{SS_LV}	SR	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	V_{SS}–0.1	V_{SS}+0.1	V
V_{DD_BV}	SR	Voltage on VDD_BV pin (regulator supply) with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	–0.3	V_{DD}+0.3	
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS})	—	V_{SS}–0.1	V_{SS}+0.1	V
V_{DD_ADC}	SR	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	V_{DD} –0.3	V_{DD}+0.3	

Table 12. Absolute maximum ratings (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	—	V_{DD}+0.3	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–10	10	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
I_{AVGSEG}	SR	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	70	mA
			V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	64	
I_{CORELV}	SR	Low voltage static current sink through VDD_BV	—	—	150	mA
$T_{STORAGE}$	SR	Storage temperature	—	–55	150	°C

Note: Stresses exceeding the recommended absolute maximum ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. During overload conditions ($V_{IN} > V_{DD}$ or $V_{IN} < V_{SS}$), the voltage on pins with respect to ground (V_{SS}) must not exceed the recommended values.

3.13 Recommended operating conditions

Table 13. Recommended operating conditions (3.3 V)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS}	SR	Digital ground on VSS_HV pins	—	0	0	V
V_{DD}(1)	SR	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	3.0	3.6	V
V_{SS_LV}(2)	SR	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	V_{SS}–0.1	V_{SS}+0.1	V
V_{DD_BV}(3)	SR	Voltage on VDD_BV pin (regulator supply) with respect to ground (V_{SS})	—	3.0	3.6	V
			Relative to V_{DD}	V_{DD}–0.1	V_{DD}+0.1	
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS})	—	V_{SS}–0.1	V_{SS}+0.1	V
V_{DD_ADC}(4)	SR	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V_{SS})	—	3.0(5)	3.6	V
			Relative to V_{DD}	V_{DD}–0.1	V_{DD}+0.1	

Table 15. LQFP thermal characteristics(1) (continued)

Symbol		C	Parameter	Conditions(2)	Pin count	Value	Unit
$R_{\theta JC}$	CC	D	Thermal resistance, junction-to-case(5)	Single-layer board - 1s	64	11	°C/W
					100	22	
					144	22	
				Four-layer board - 2s2p	64	11	
					100	22	
					144	22	
Ψ_{JB}	CC	D	Junction-to-board thermal characterization parameter, natural convection	Single-layer board - 1s	64	TBD	°C/W
					100	33	
					144	34	
				Four-layer board - 2s2p	64	TBD	
					100	34	
					144	35	
Ψ_{JC}	CC	D	Junction-to-case thermal characterization parameter, natural convection	Single-layer board - 1s	64	TBD	°C/W
					100	9	
					144	10	
				Four-layer board - 2s2p	64	TBD	
					100	9	
					144	10	

1. Thermal characteristics are based on simulation.
2. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C
3. Junction-to-ambient thermal resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package.
4. Junction-to-board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.
5. Junction-to-case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.

3.14.2 Power considerations

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using *Equation 1*:

Equation 1 $T_J = T_A + (P_D \times R_{\theta JA})$

Where:

T_A is the ambient temperature in °C.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD}, expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Table 24. I/O weight[1] (continued)

Supply segment			Pad	LQFP144/LQFP100				LQFP64[2]			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 144	LQFP 100	LQFP 64		SRC[3] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
1	—	—	PG[9]	9%	—	10%	—	—	—	—	—
	—	—	PG[8]	9%	—	11%	—	—	—	—	—
	1	—	PC[11]	9%	—	11%	—	—	—	—	—
		1	PC[10]	9%	13%	11%	12%	9%	13%	11%	12%
	—	—	PG[7]	10%	14%	11%	12%	—	—	—	—
	—	—	PG[6]	10%	14%	12%	12%	—	—	—	—
	1	1	PB[0]	10%	14%	12%	12%	10%	14%	12%	12%
			PB[1]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[9]	10%	—	12%	—	—	—	—	—
	—	—	PF[8]	10%	15%	12%	13%	—	—	—	—
	—	—	PF[12]	10%	15%	12%	13%	—	—	—	—
	1	1	PC[6]	10%	—	12%	—	10%	—	12%	—
			PC[7]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[10]	10%	14%	12%	12%	—	—	—	—
	—	—	PF[11]	10%	—	11%	—	—	—	—	—
	1	1	PA[15]	9%	12%	10%	11%	9%	12%	10%	11%
	—	—	PF[13]	8%	—	10%	—	—	—	—	—
	1	1	PA[14]	8%	11%	9%	10%	8%	11%	9%	10%
			PA[4]	8%	—	9%	—	8%	—	9%	—
			PA[13]	7%	10%	9%	9%	7%	10%	9%	9%
			PA[12]	7%	—	8%	—	7%	—	8%	—

Table 24. I/O weight[1] (continued)

Supply segment			Pad	LQFP144/LQFP100				LQFP64[2]			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 144	LQFP 100	LQFP 64		SRC[3] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
	2	2	PB[9]	1%	—	1%	—	1%	—	1%	—
			PB[8]	1%	—	1%	—	1%	—	1%	—
			PB[10]	6%	—	7%	—	6%	—	7%	—
	—	—	PF[0]	6%	—	7%	—	—	—	—	—
	—	—	PF[1]	7%	—	8%	—	—	—	—	—
	—	—	PF[2]	7%	—	8%	—	—	—	—	—
	—	—	PF[3]	7%	—	9%	—	—	—	—	—
	—	—	PF[4]	8%	—	9%	—	—	—	—	—
	—	—	PF[5]	8%	—	10%	—	—	—	—	—
	—	—	PF[6]	8%	—	10%	—	—	—	—	—
	—	—	PF[7]	9%	—	10%	—	—	—	—	—
	2	—	PD[0]	1%	—	1%	—	—	—	—	—
		—	PD[1]	1%	—	1%	—	—	—	—	—
		—	PD[2]	1%	—	1%	—	—	—	—	—
		—	PD[3]	1%	—	1%	—	—	—	—	—
2		—	PD[4]	1%	—	1%	—	—	—	—	—
		—	PD[5]	1%	—	1%	—	—	—	—	—
		—	PD[6]	1%	—	1%	—	—	—	—	—
		—	PD[7]	1%	—	1%	—	—	—	—	—
		—	PD[8]	1%	—	1%	—	—	—	—	—
		2	PB[4]	1%	—	1%	—	1%	—	1%	—
			PB[5]	1%	—	1%	—	1%	—	2%	—
			PB[6]	1%	—	1%	—	1%	—	2%	—
			PB[7]	1%	—	1%	—	1%	—	2%	—
		—	PD[9]	1%	—	1%	—	—	—	—	—
		—	PD[10]	1%	—	1%	—	—	—	—	—
		—	PD[11]	1%	—	1%	—	—	—	—	—
		2	PB[11]	11%	—	13%	—	17%	—	21%	—
		—	PD[12]	11%	—	13%	—	—	—	—	—
		2	PB[12]	11%	—	13%	—	18%	—	21%	—
		—	PD[13]	10%	—	12%	—	—	—	—	—

3.17 Power management electrical characteristics

3.17.1 Voltage regulator electrical characteristics

The device implements an internal voltage regulator to generate the low voltage core supply V_{DD_LV} from the high voltage ballast supply V_{DD_BV}. The regulator itself is supplied by the common I/O supply V_{DD}. The following supplies are involved:

- HV—High voltage external power supply for voltage regulator module. This must be provided externally through VDD_HV power pin.
- BV—High voltage external power supply for internal ballast module. This must be provided externally through VDD_BV power pin. Voltage values should be aligned with V_{DD}.
- LV—Low voltage internal power supply for core, FMPLL and flash digital logic. This is generated by the internal voltage regulator but provided outside to connect stability capacitor. It is further split into four main domains to ensure noise isolation between critical LV modules within the device:
  - LV_COR—Low voltage supply for the core. It is also used to provide supply for FMPLL through double bonding.
  - LV_CFLA—Low voltage supply for code flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
  - LV_DFLA—Low voltage supply for data flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
  - LV_PLL—Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.

3.19.3 Start-up/Switch-off timings

Table 33. Start-up time/Switch-off time

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
$T_{FLARSTEXIT}$	CC	T	Delay for Flash module to exit reset mode	Code Flash	—	—	125	µs
		T		Data Flash	—	—	125	
$T_{FLALPEXIT}$	CC	T	Delay for Flash module to exit low-power mode	Code Flash	—	—	0.5	
		T		Data Flash	—	—	0.5	
$T_{FLAPDEXIT}$	CC	T	Delay for Flash module to exit power-down mode	Code Flash	—	—	30	
		T		Data Flash	—	—	30	
$T_{FLALPENTRY}$	CC	T	Delay for Flash module to enter low-power mode	Code Flash	—	—	0.5	
		T		Data Flash	—	—	0.5	
$T_{FLAPDENTRY}$	CC	T	Delay for Flash module to enter power-down mode	Code Flash	—	—	1.5	
		T		Data Flash	—	—	1.5	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

3.20 Electromagnetic compatibility (EMC) characteristics

Susceptibility tests are performed on a sample basis during product characterization.

3.20.1 Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user apply EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

- Software recommendations: The software flowchart must include the management of runaway conditions such as:
  - Corrupted program counter
  - Unexpected reset
  - Critical data corruption (control registers...)
- Prequalification trials: Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the reset pin or the oscillator pins for 1 second.

  To complete these trials, ESD stress can be applied directly on the device. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note *Software Techniques For Improving Microcontroller EMC Performance* (AN1015)).

Table 38. Fast external crystal oscillator (4 to 16 MHz) electrical characteristics (continued)

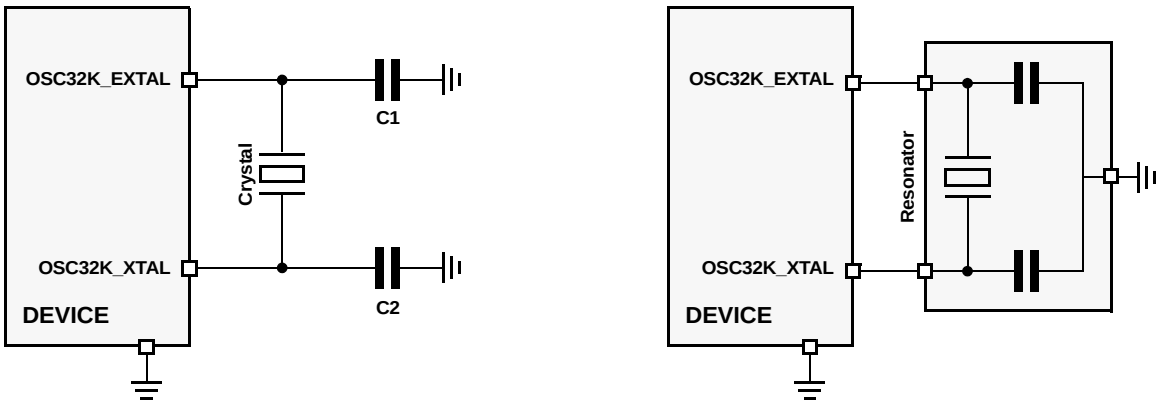
Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input high level CMOS (Schmitt Trigger)	Oscillator bypass mode	$0.65V_{DD}$	—	$V_{DD}+0.4$	V
V_{IL}	SR	P	Input low level CMOS (Schmitt Trigger)	Oscillator bypass mode	–0.4	—	$0.35V_{DD}$	V

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified
2. Stated values take into account only analog module consumption but not the digital contributor (clock tree and enabled peripherals)

3.22 Slow external crystal oscillator (32 kHz) electrical characteristics

The device provides a low power oscillator/resonator driver.

Figure 15. Crystal oscillator and resonator connection scheme



Note: OSC32K_XTAL/OSC32K_EXTAL must not be directly used to drive external circuits.

Figure 16. Equivalent circuit of a quartz crystal

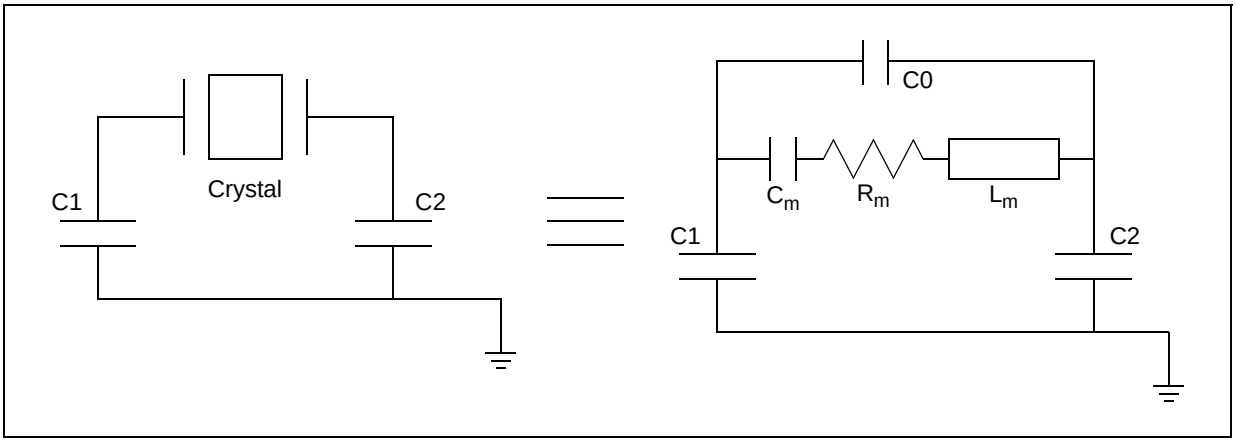
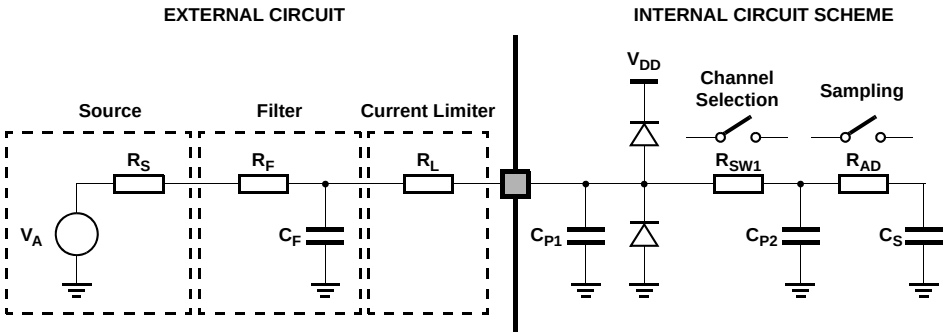


Table 39. Crystal motional characteristics(1)

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
L_m	Motional inductance	—	—	11.796	—	KH
C_m	Motional capacitance	—	—	2	—	fF
C1/C2	Load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground(2)	—	18	—	28	pF
R_m(3)	Motional resistance	AC coupled @ C0 = 2.85 pF(4)	—	—	65	kW
		AC coupled @ C0 = 4.9 pF(4)	—	—	50	
		AC coupled @ C0 = 7.0 pF(4)	—	—	35	
		AC coupled @ C0 = 9.0 pF(4)	—	—	30	

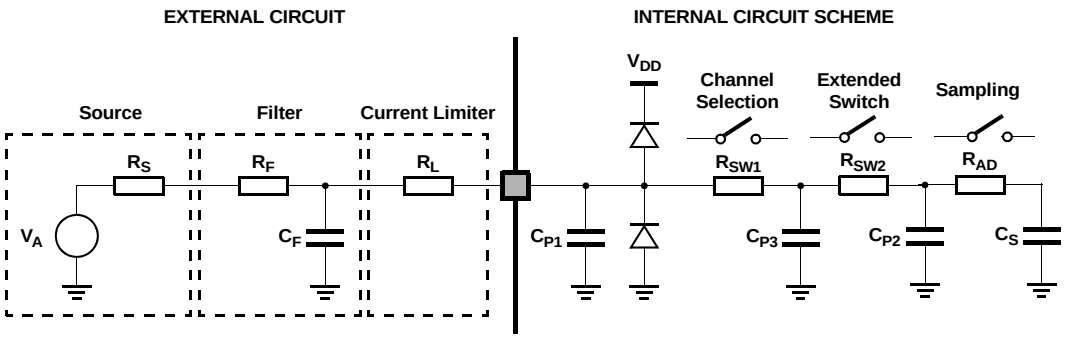
1. Crystal used: Epson Toyocom MC306
2. This is the recommended range of load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground. It includes all the parasitics due to board traces, crystal and package.
3. Maximum ESR (R_m) of the crystal is 50 kΩ
4. C0 includes a parasitic capacitance of 2.0 pF between OSC32K_XTAL and OSC32K_EXTAL pins

Figure 19. Input equivalent circuit (precise channels)



R_S: Source impedance
R_F: Filter resistance
C_F: Filter capacitance
R_L: Current limiter resistance
R_{SW1}: Channel selection switch impedance
R_{AD}: Sampling switch impedance
C_P: Pin capacitance (two contributions, C_{P1} and C_{P2})
C_S: Sampling capacitance

Figure 20. Input equivalent circuit (extended channels)



R_S: Source impedance
R_F: Filter resistance
C_F: Filter capacitance
R_L: Current limiter resistance
R_{SW1}: Channel selection switch impedance (two contributions, R_{SW1} and R_{SW2})
R_{AD}: Sampling switch impedance
C_P: Pin capacitance (two contributions, C_{P1}, C_{P2} and C_{P3})
C_S: Sampling capacitance

Table 45. ADC conversion characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{SS_ADC}	SR	—	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS})[2]	—	–0.1	—	0.1	V
V_{DD_ADC}	SR	—	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V_{SS})	—	V_{DD}–0.1	—	V_{DD}+0.1	V
V_{AINx}	SR	—	Analog input voltage[3]	—	V_{SS_ADC}–0.1	—	V_{DD_ADC}+0.1	V
f_{ADC}	SR	—	ADC analog frequency	—	6	—	32 + 4%	MHz
Δ_{ADC_SYS}	SR	—	ADC digital clock duty cycle (ipg_clk)	ADCLKSEL = 1[4]	45	—	55	%
I_{ADCPWD}	SR	—	ADC0 consumption in power down mode	—	—	—	50	µA
I_{ADCRUN}	SR	—	ADC0 consumption in running mode	—	—	—	4	mA
t_{ADC_PU}	SR	—	ADC power up delay	—	—	—	1.5	µs
t_s	CC	T	Sampling time[5]	f_{ADC} = 32 MHz, INPSAMP = 17	0.5	—		µs
				f_{ADC} = 6 MHz, INPSAMP = 255	—	—	42	
t_c	CC	P	Conversion time[6]	f_{ADC} = 32 MHz, INPCMP = 2	0.625	—		µs
C_S	CC	D	ADC input sampling capacitance	—	—	—	3	pF
C_{P1}	CC	D	ADC input pin capacitance 1	—	—	—	3	pF
C_{P2}	CC	D	ADC input pin capacitance 2	—	—	—	1	pF
C_{P3}	CC	D	ADC input pin capacitance 3	—	—	—	1	pF
R_{SW1}	CC	D	Internal resistance of analog source	—	—	—	3	kΩ
R_{SW2}	CC	D	Internal resistance of analog source	—	—	—	2	kΩ
R_{AD}	CC	D	Internal resistance of analog source	—	—	—	2	kΩ

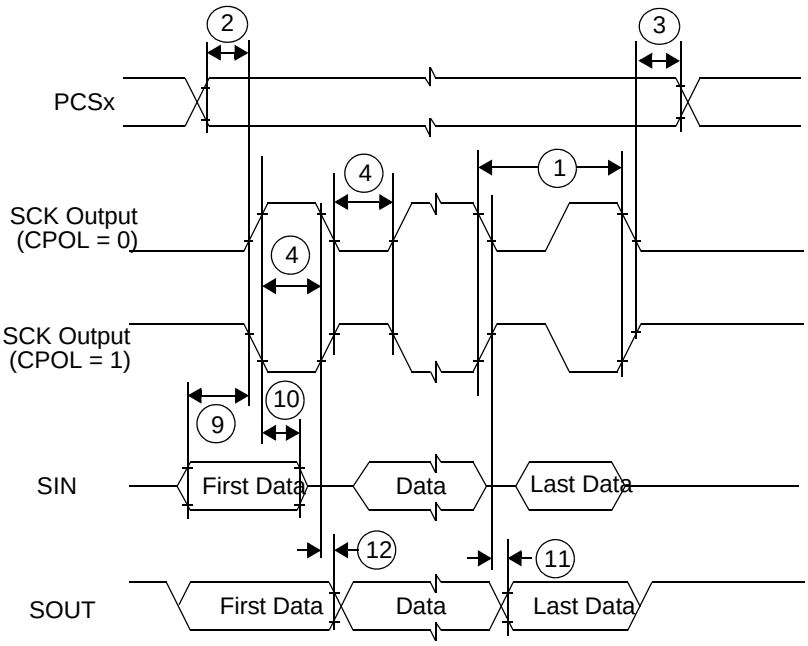
3.27.2 DSPI characteristics

Table 46. On-chip peripherals current consumption(1)

Symbol		C	Parameter	Conditions		Typical value(2)	Unit
$I_{DD\_BV(CAN)}$	CC	T	CAN (FlexCAN) supply current on VDD_BV	Bitrate: 500 Kbyte/s	Total (static + dynamic) consumption: – FlexCAN in loop-back mode – XTAL @ 8 MHz used as CAN engine clock source – Message sending period is 580 µs	8 * f_{periph} + 85	µA
				Bitrate: 125 Kbyte/s		8 * f_{periph} + 27	
$I_{DD\_BV(eMIOS)}$	CC	T	eMIOS supply current on VDD_BV	Static consumption: – eMIOS channel OFF – Global prescaler enabled		29 * f_{periph}	µA
				Dynamic consumption: – It does not change varying the frequency (0.003 mA)		3	
$I_{DD\_BV(SCI)}$	CC	T	SCI (LINFlex) supply current on VDD_BV	Total (static + dynamic) consumption: – LIN mode – Baudrate: 20 Kbyte/s		5 * f_{periph} + 31	µA
$I_{DD\_BV(SPI)}$	CC	T	SPI (DSPI) supply current on VDD_BV	Ballast static consumption (only clocked)		1	µA
				Ballast dynamic consumption (continuous communication): – Baudrate: 2 Mbit/s – Transmission every 8 µs – Frame: 16 bits		16 * f_{periph}	
$I_{DD\_BV(ADC)}$	CC	T	ADC supply current on VDD_BV	V_{DD} = 5.5 V	Ballast static consumption (no conversion)	41 * f_{periph}	µA
					Ballast dynamic consumption (continuous conversion)(3)	5 * f_{periph}	
$I_{DD\_HV\_ADC(ADC)}$	CC	T	ADC supply current on VDD_HV_ADC	V_{DD} = 5.5 V	Analog static consumption (no conversion)	2 * f_{periph}	µA
					Analog dynamic consumption (continuous conversion)	75 * f_{periph} + 32	
$I_{DD\_HV(FLASH)}$	CC	T	Code Flash + Data Flash supply current on VDD_HV	V_{DD} = 5.5 V	—	8.21	mA
$I_{DD\_HV(PLL)}$	CC	T	PLL supply current on VDD_HV	V_{DD} = 5.5 V	—	30 * f_{periph}	µA

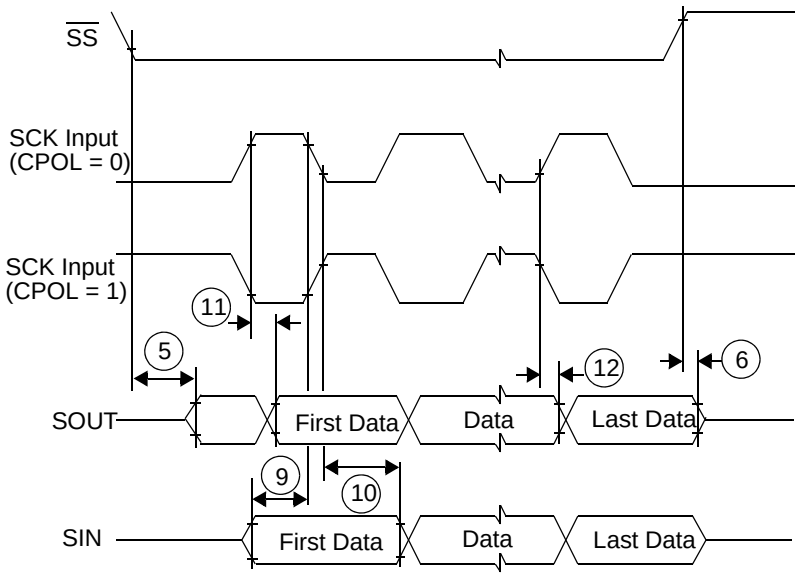
1. Operating conditions: T_A = 25 °C, f_{periph} = 8 MHz to 64 MHz
2. f_{periph} is an absolute value.

Figure 23. DSPI classic SPI timing – master, CPHA = 0



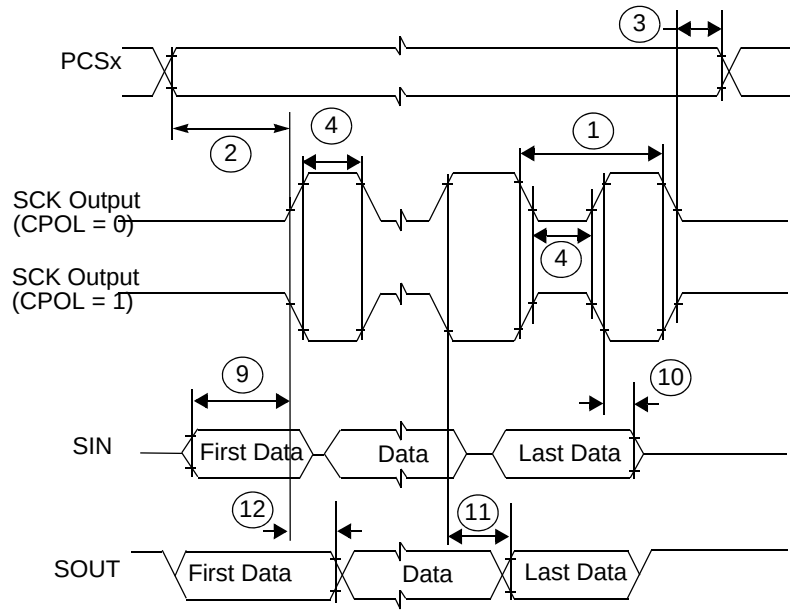
Note: Numbers shown reference *Table 47*.

Figure 26. DSPI classic SPI timing – slave, CPHA = 1



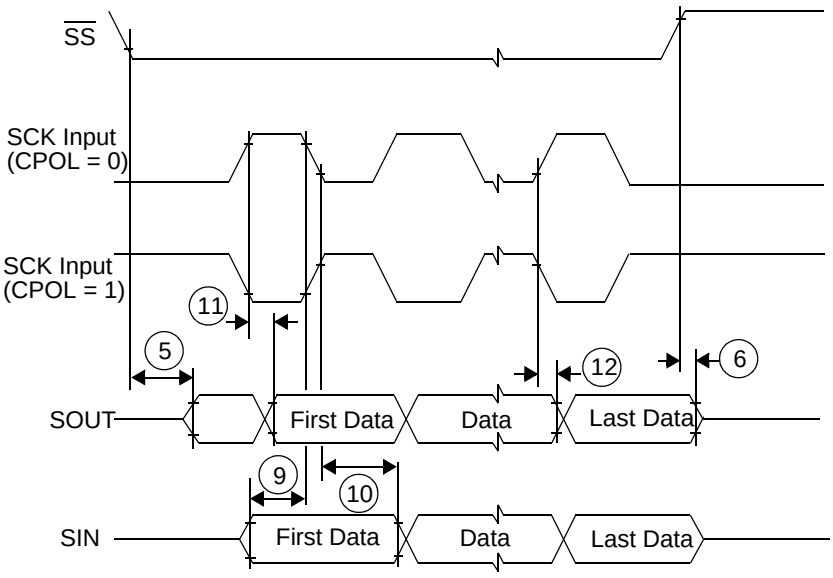
Note: Numbers shown reference *Table 47*.

Figure 27. DSPI modified transfer format timing – master, CPHA = 0



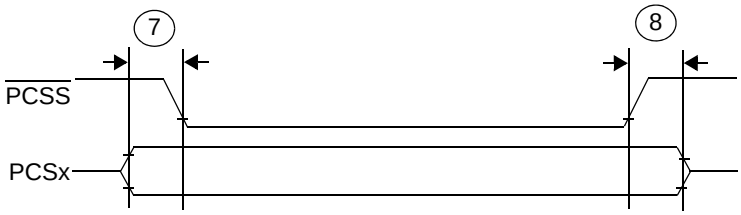
Note: Numbers shown reference *Table 47*.

Figure 30. DSPI modified transfer format timing – slave, CPHA = 1



Note: Numbers shown reference *Table 47*.

Figure 31. DSPI PCS strobe ($\overline{\text{PCSS}}$) timing



Note: Numbers shown reference *Table 47*.

3.27.3 Nexus characteristics

Table 48. Nexus characteristics

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
1	t_{TCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{MCYC}	CC	D	MCKO cycle time	32	—	—	ns
3	t_{MDOV}	CC	D	MCKO low to MDO data valid	—	—	8	ns

Table 50. LQFP64 mechanical data (continued)

Symbol	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
D1	9.8	10	10.2	0.3858	0.3937	0.4016
D3	—	7.5	—	—	0.2953	—
E	11.8	12	12.2	0.4646	0.4724	0.4803
E1	9.8	10	10.2	0.3858	0.3937	0.4016
E3	—	7.5	—	—	0.2953	—
e	—	0.5	—	—	0.0197	—
L	0.45	0.6	0.75	0.0177	0.0236	0.0295
L1	—	1	—	—	0.0394	—
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	—	—	0.08	—	—	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.